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would

at least an n-type semiconductor layer, an active layer and a p-type semiconductor layer deposited in this order, and a p-side electrode and an n-side electrode, wherein the p-side electrode of the first laser unit is electrically connected to the n-side electrode of the second laser unit and the n-side electrode of the first laser unit is electrically connected to the p-side electrode of the second laser unit.

2. (Amended) The semiconductor laser device according to claim 1, further comprising:  
a first connecting layer interconnecting said p-side electrode of the first laser unit and said n-side electrode of the second laser unit; and  
a second connecting layer interconnecting between said p-side electrode of the second laser unit and said n-side electrode of the first laser unit.

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4. (Twice Amended) The semiconductor laser device according to claim 2, wherein at least one of said first and said second connecting layers has a Schottky barrier.

5. (Twice Amended) The semiconductor laser device according to claim 1, wherein at least one of the first and second laser units has a Schottky barrier between the p-side electrode and the p-type semiconductor layer.

6. (Twice Amended) The semiconductor laser device according to claim 1, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

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10 ~~14~~ (Amended) The semiconductor laser device according to claim 2, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

11 ~~15~~ (Amended) The semiconductor laser device according to claim 3, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.

12 ~~16~~ (Amended) The semiconductor laser device according to claim 4, wherein at least one of the first and second laser units is a semiconductor laser having a gallium (GaN) system semiconductor deposited.

13 ~~17~~ (Amended) The semiconductor laser device according to claim 5, wherein at least one of the first and second laser units is a semiconductor laser having a gallium nitride (GaN) system semiconductor deposited.